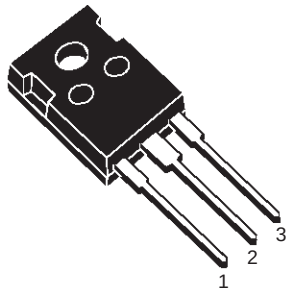
STW14NM50

N-CHANNEL 500V - 0.32Ω - 14A TO-247
MDmesh™ Power MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW14NM50	500V	< 0.35Ω	14 A

- TYPICAL $R_{DS}(on)$ = 0.32Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTORING YIELDS



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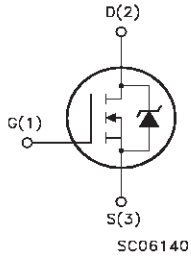
INTERNAL SCHEMATIC DIAGRAM



DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprierati strip technique yields overall dynamic performance that is significantly better than that of similar completition's products.

APPLICATIONS

The MDmesh™ family is very suitablr for increase the power density of high voltage converters allowing system miniaturization and higher efficiencies.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	500	V
V_{GS}	Gate- source Voltage	±30	V
I_D	Drain Current (continuos) at T_C = 25°C	14	A
I_D	Drain Current (continuos) at T_C = 100°C	8.8	A
I_{DM} (1)	Drain Current (pulsed)	56	A
P_{TOT}	Total Dissipation at T_C = 25°C	160	W
	Derating Factor	1.28	W/°C
dv/dt	Peak Diode Recovery voltage slope	6	V/ns
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(*)Limited only by maximum temperature allowed

(1)I_{SD} ≤12A, di/dt ≤100A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ $T_{JMAX.}$

This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.78	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	0.1	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	12	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	400	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	500			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 6A		0.3	0.35	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, V_{GS} = 10V	14			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 6A		5.2		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1000		pF
C_{oss}	Output Capacitance			180		pF
C_{rss}	Reverse Transfer Capacitance			25		pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 250V, I_D = 6A		20		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		10		ns
Q_g	Total Gate Charge	V_{DD} = 400V, I_D = 12A, V_{GS} = 10V		28		nC
Q_{gs}	Gate-Source Charge			8		nC
Q_{gd}	Gate-Drain Charge			15		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 400V, I_D = 12A, R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		19		ns
t_f	Fall Time			8		ns
t_c	Cross-over Time			18		ns

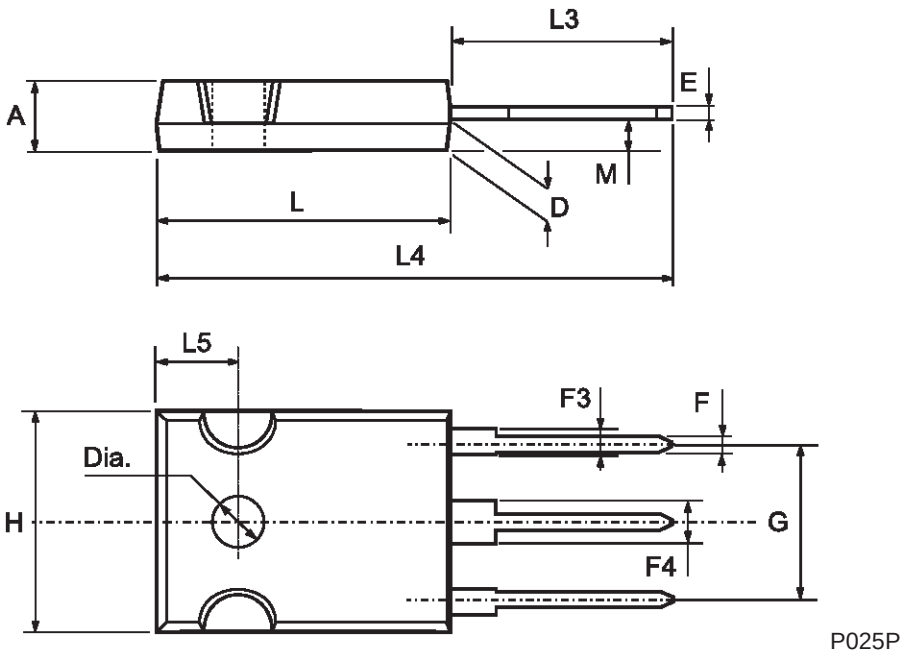
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				12	A
I_{SDM} (1)	Source-drain Current (pulsed)				48	A
V_{SD} (2)	Forward On Voltage	I_{SD} = 12A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 12A, di/dt = 100A/µs, V_{DD} = 100V, T_j = 150°C (see test circuit, Figure 5)		350		ns
Q_{rr}	Reverse Recovery Charge			5.25		µC
I_{RRM}	Reverse Recovery Current			30		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



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